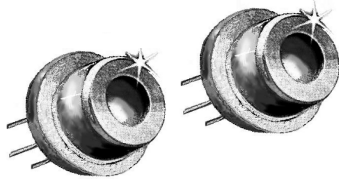


LASER DIODE FARL-300M-808-50



FARL-300M-808-50 is 808nm high power quantum well fabricated by MOCVD semiconductor laser. Low threshold current and high slope efficiency contribute to low operating current enhancing reliability.

FARL-300M-808-50 is a CW laser suitable for application in pumping, medical and other opto-electronic systems.

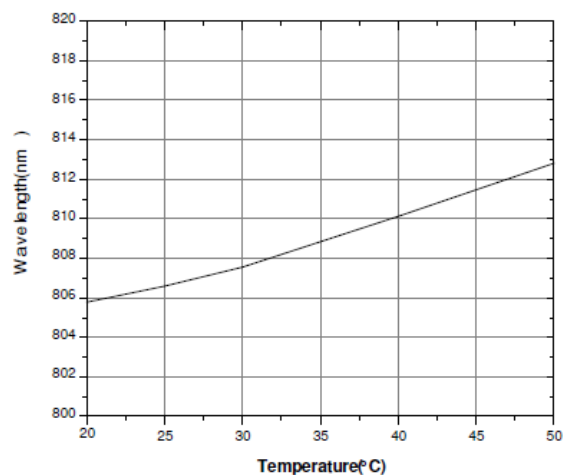
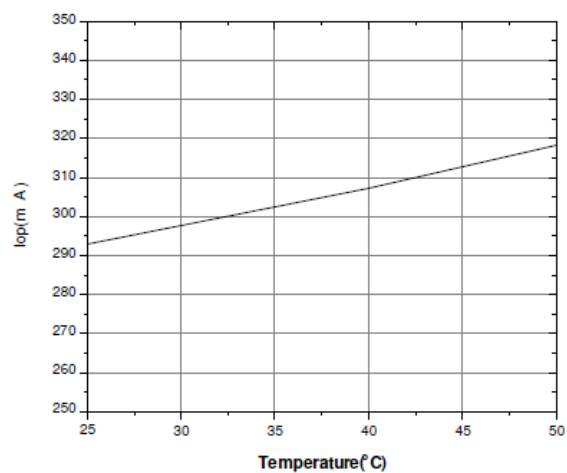
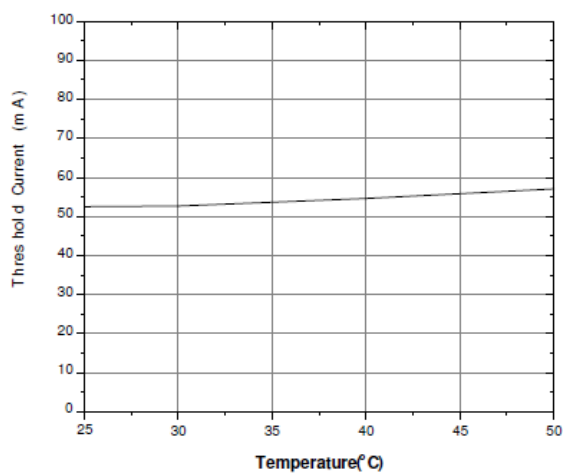
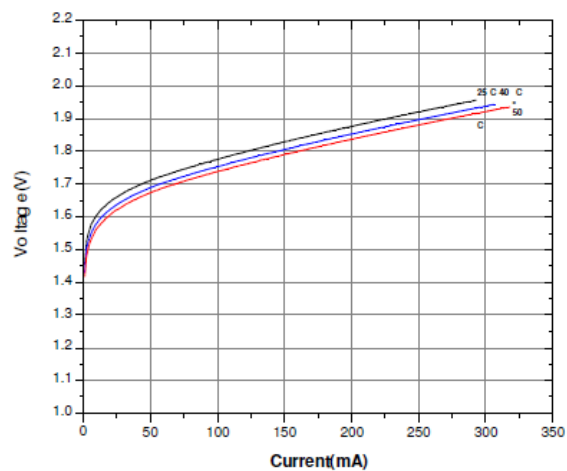
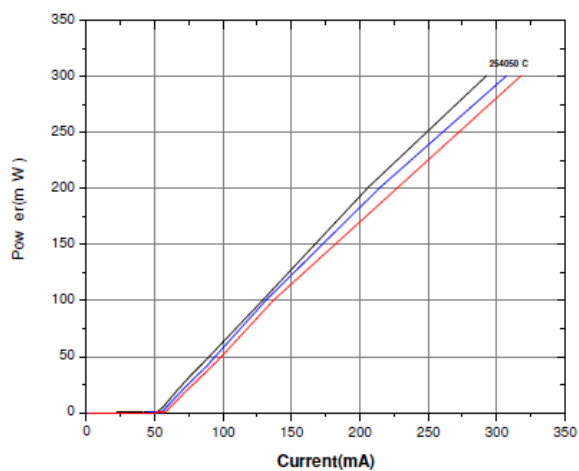
Specification (T = 25°C)

Parameter	Symbol	Min	Typ	Max	Unit
Optical output power	P_{out}			300	mW
Wavelength	λ	805	808	811	nm
Threshold current	I_{th}		65	80	mA
Forward current	I_f	-	320	360	mA
Forward voltage	V_f	-	1.95	2.2	V
Beam divergence parallel	$\Theta_{ }$		8.0	11	°
Beam divergence perpendicular	Θ_{\perp}	-	39	48	°
Positional accuracy	$\Delta X, \Delta Y, \Delta Z$	-	-	±80	μm
Differential efficiency	dPo/dIop	0.8	1.2		mW/mA

Additional information

- wavelength drift under temperature change - <0,18nm/°C
- LD reverse voltage - 2V
- operating temperature - -10°C to +50°C
- storage temperature - -40°C to +85°C

TYPICAL PERFORMANCE



PACKAGE SPECIFICATION

Package 5.6mm

